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## \*BIBDATASHEET\*

CONFIRMATION NO. 3693

Bib Data Sheet

SERIAL NUMBER 10/612,642	FILING DATE 07/01/2003  RULE	CLASS 438	GROUP ART UNIT 2812	ATTORNEY DOCKET NO. 007612 USA/ETCH/SILICON
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## APPLICANTS

Wei Liu, San Jose, CA;

David S. L. Mui, Fremont, CA;

Lance A. Scudder, Santa Clara, CA; Paul B. Comita, Menlo Park, CA;

Arkadii V. Samoilov, Sunnyvale, CA;

Babak Adibi, Los Altos, CA;

## \*\* CONTINUING DATA \*\*\*\*\*

This appln claims benefit of 60/393,393 07/02/2002 *WLL*

## \*\* FOREIGN APPLICATIONS \*\*\*\*\*

*None WLL*

## IF REQUIRED, FOREIGN FILING LICENSE GRANTED

\*\* 09/26/2003

Foreign Priority claimed <input type="checkbox"/> yes <input checked="" type="checkbox"/> no	STATE OR COUNTRY CA	SHEETS DRAWING 11	TOTAL CLAIMS 30	INDEPENDENT CLAIMS 5
35 USC 119 (a-d) conditions met <input type="checkbox"/> yes <input checked="" type="checkbox"/> no <input type="checkbox"/> Met after Allowance <i>WLL</i>				
Verified and Acknowledged	Examiner's Signature	Initials		

## ADDRESS

44182

MOSER, PATTERSON &amp; SHERIDAN, LLP

APPLIED MATERIALS INC

595 SHREWSBURY AVE

SUITE 100

SHREWSBURY, NJ

07702

## TITLE

Method for fabricating an ultra shallow junction of a field effect transistor

☐ All Fees